

RL78/G1G RENESAS MCU R01DS0241EJ0130 Rev. 1.30 Sep 30, 2016

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD = single power supply voltage of 2.7 to 5.5 V
- · HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

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- · CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high-speed (0.04167 μs : @ 24 MHz operation with high-speed on-chip oscillator) to low-speed (1.0 μs : @1 MHz operation with high-speed on-chip oscillator)
- Multiply/divide/multiply & accumulate instructions are supported.
- · Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 1.5 KB

Code flash memory

- Code flash memory: 8 to 16 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- · Self-programming (flash shield window function)

High-speed on-chip oscillator

- Select from 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 4 MHz, and 1 MHz
- High accuracy: ±2.0%

Operating ambient temperature

• TA = -40 to $+85^{\circ}$ C

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 6 levels)

Event link controller (ELC)

 Event signals of 18 to 19 types can be linked to the specified peripheral function.

Serial interfaces

- CSI: 1 channel
- · UART: 2 channels
- Simplified I²C: 1 channel

Timer

- 16-bit timer: 7 channels (Timer Array Unit (TAU): 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels)
- 12-bit interval timer: 1 channel
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (VDD = 2.7 to 5.5 V)
- · Analog input: 8 to 12 channels
- Internal reference voltage (1.45 V) and temperature sensorNote

Note: Selectable only in HS (high-speed main) mode.

Comparator

- 2 channels
- The voltage from a dedicated 8-bit DAC (resolution of 256 with VDD/AVREFP or VSS/AVREFM as the internally generated reference voltage) can be selected as the reference voltage.

Programmable gain amplifier

I/O port

- I/O port: 26 to 40
- Can be set to N-ch open drain, TTL input buffer, and onchip pull-up resistor
- Different potential interface: Can connect to a 2.5/3 V device
- On-chip key interrupt function
- · On-chip clock output/buzzer output controller

Others

• On-chip BCD (binary-coded decimal) correction circuit

Remark: The function mounted depend on the product.

See 1.6 Outline of Functions.



○ ROM, RAM capacities

Flash ROM	RAM	30 pins	32 pins	44 pins
16 KB	1.5 KB Note	R5F11EAAASP	R5F11EBAAFP	R5F11EFAAFP
8 KB		R5F11EA8ASP	R5F11EB8AFP	R5F11EF8AFP

Note This is 630 bytes when the self-programming function is used.

1.2 List of Part Numbers

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1G

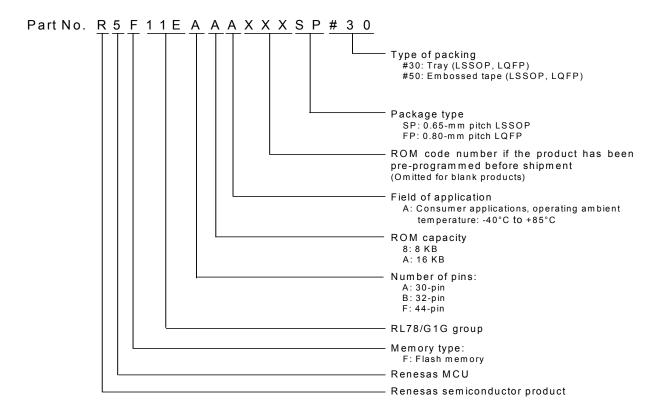


Table 1 - 1 Orderable Part Numbers

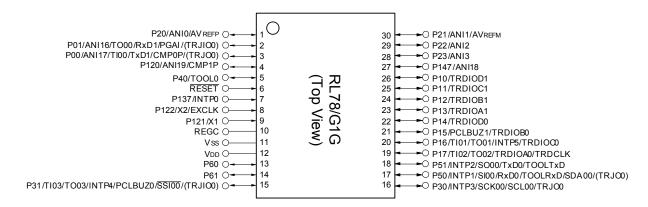
Pin Count	Package	Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm)	R5F11EFAAFP#30, R5F11EFAAFP#50
		R5F11EF8AFP#30, R5F11EF8AFP#50
32 pins	32-pin plastic LQFP (7 × 7 mm)	R5F11EBAAFP#30, R5F11EBAAFP#50
		R5F11EB8AFP#30, R5F11EB8AFP#50
30 pins	30-pin plastic LSSOP (7.62 mm (300))	R5F11EAAASP#30, R5F11EAAASP#50
		R5F11EA8ASP#30, R5F11EA8ASP#50

1.3 Pin Configuration (Top View)

1.3.1 **30-pin products**

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• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

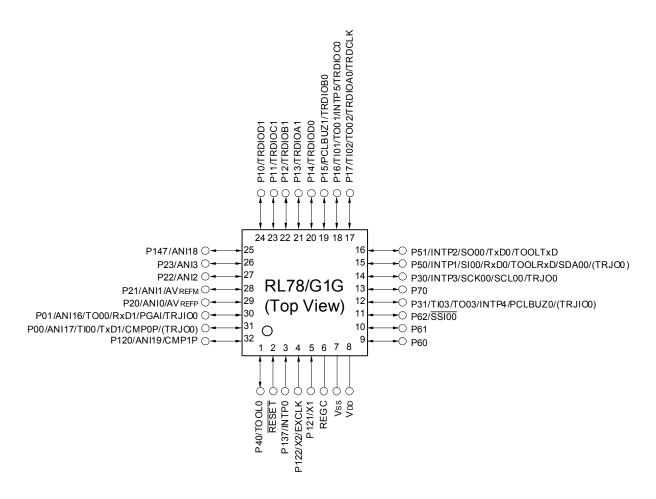
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. The functions in parentheses shown in the above figure can be assigned by setting peripheral I/O redirection register 1 (PIOR1).

1.3.2 32-pin products

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• 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

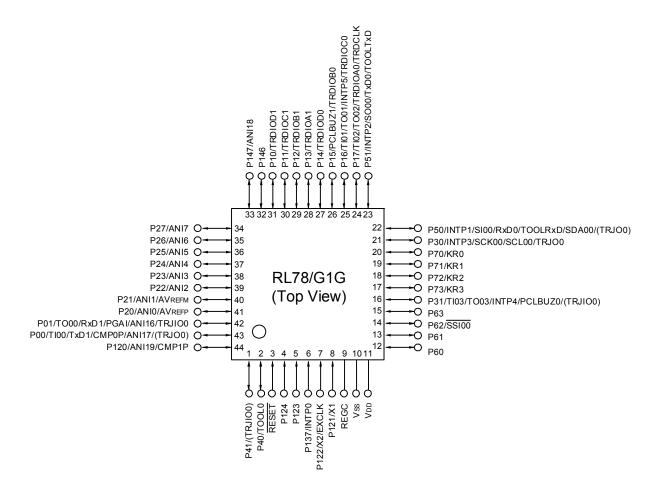
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. The functions in parentheses shown in the above figure can be assigned by setting peripheral I/O redirection register 1 (PIOR1).

1.3.3 44-pin products

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• 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. The functions in parentheses shown in the above figure can be assigned by setting peripheral I/O redirection register 1 (PIOR1).

1.4 Pin Identification

ANI0 to ANI7, ANI16 to ANI19: Analog input

AVREFM: A/D converter reference potential (- side) input
AVREFP: A/D converter reference potential (+ side) input

EXCLK: External clock input (main system clock)

INTP0 to INTP5: External interrupt input

KR0 to KR3: Key Return P00, P01: Port 0 P10 to P17: Port 1 P20 to P27: Port 2 P30, P31: Port 3 P40, P41: Port 4 P50, P51: Port 5 P60 to P63: Port 6 P70 to P73: Port 7 P120 to P124: Port 12 P137: Port 13 P146, P147: Port 14

PCLBUZ0, PCLBUZ1: Programmable clock output/buzzer output

REGC: Regulator capacitance

RESET: Reset

RxD0, RxD1: Receive data

SCK00: Serial clock input/output
SCL00: Serial clock output
SDA00: Serial data input/output

SI00: Serial data input SO00: Serial data output

SSI00: Serial interface chip select input

TI00 to TI03: Timer input
TO00 to TO03, TRJO0: Timer output

TOOL0: Data input/output for tool

TOOLRxD, TOOLTxD: Data input/output for external device

TRDCLK: Timer external input clock

 $TRDIOA0,\,TRDIOB0,\,TRDIOC0,\,TRDIOD0,: Timer\ input/output$

TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1,

TRJIO0

TxD0, TxD1: Transmit data

CMP0P, CMP1P: Comparator input

PGAI: PGA input

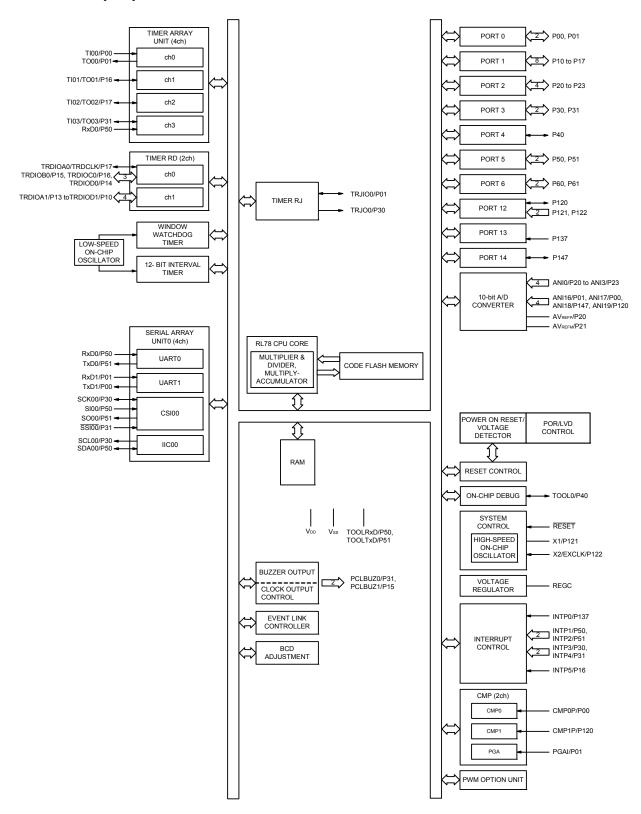
VDD: Power supply

Vss: Ground

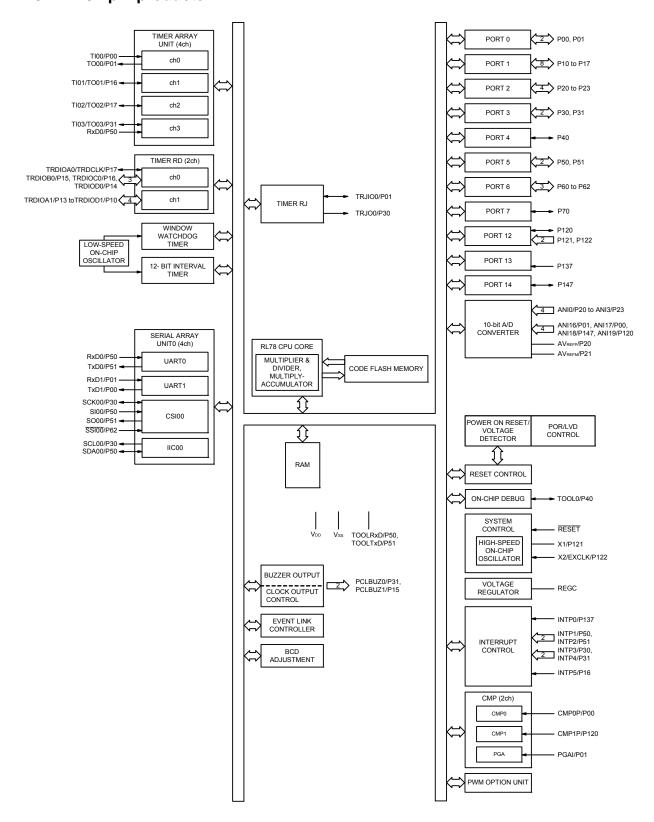
X1, X2: Crystal oscillator (main system clock)

1.5 Block Diagram

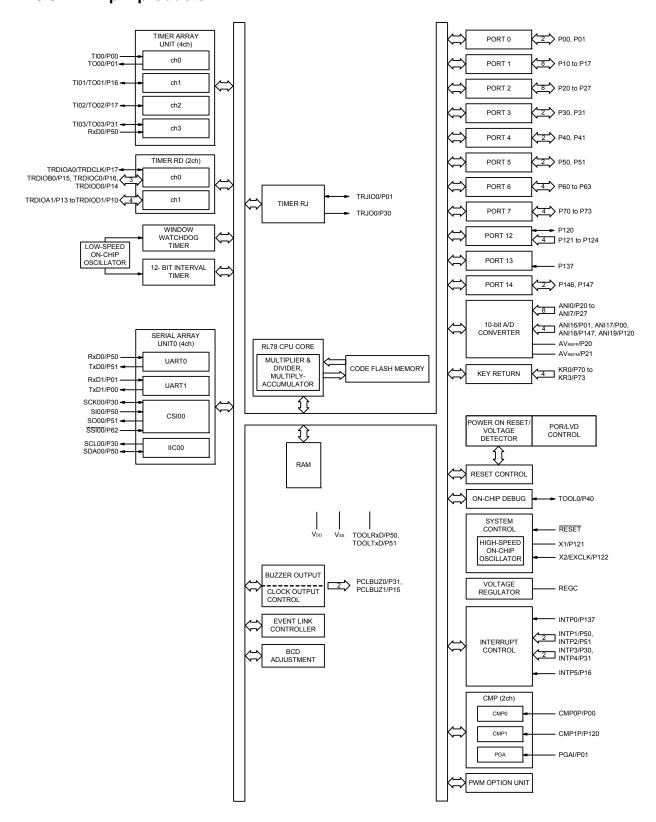
1.5.1 **30-pin products**



1.5.2 32-pin products



1.5.3 **44-pin products**



1.6 Outline of Functions

[30-pin, 32-pin, 44-pin products (code flash memory 8 KB to 16 KB)]

Caution The above outline of the functions applies when peripheral I/O redirection register 1 (PIOR1) is set to 00H.

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		30-pin	32-pin	44-pin				
	Item	R5F11EA8ASP, R5F11EAAASP	R5F11EB8AFP, R5F11EBAAFP	R5F11EF8AFP, R5F11EFAAFP				
Code flash m	nemory (KB)		8 to 16					
RAM (KB)			1.5					
Address space	ce	1 MB						
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, LS (low-speed main) mode: 1 to HS (high-speed main) mode: 1 t	, ,	(EXCLK)				
	High-speed on-chip oscillator clock (fiH)	LS (low-speed main) mode: 1 to HS (high-speed main) mode: 1	,					
Low-speed o	n-chip oscillator clock	15 kHz (TYP.): VDD = 2.7 to 5.5	V					
General-purp	oose register	8 bits × 32 registers (8 bits × 8	registers × 4 banks)					
Minimum ins	truction execution	0.04167 μs (High-speed on-chip oscillator clock: fiн = 24 MHz operation)						
time		0.05 μs (High-speed system clock: fмx = 20 MHz operation)						
Instruction se	et	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 						
I/O port	Total	26	28	40				
	CMOS I/O	23	25	35				
	CMOS input	3	3	5				
	CMOS output		_					
	N-ch open-drain I/O (6 V tolerance)		_					
Timer	16-bit timer	7 channels (TAU: 4 channels, Timer RJ: 1 c	channel, Timer RD: 2 channels)					
	Watchdog timer	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels						

Caution Since a library is used when rewriting the flash memory using the user program, flash ROM and RAM areas are used. Refer to the RL78 Family Flash Self-Programming Library Type01 User's Manual before using these products.

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		<u> </u>						
		30-pin	32-pin	44-pin				
	Item	R5F11EA8ASP,	R5F11EB8AFP,	R5F11EF8AFP,				
		R5F11EAAASP	R5F11EBAAFP	R5F11EFAAFP				
Clock output/	buzzer output		2					
		• 2.44 kHz, 4.88 kHz, 9.77 kHz,	1.25 MHz, 2.5 MHz, 5 MHz,	10 MHz				
		(Main system clock: fmain = 20) MHz operation)					
8/10-bit resol	ution A/D converter	8 channels		12 channels				
Comparator		2 channels		·				
PGA		1 channel						
Serial interfac	ce	CSI: 1 channel/UART0: 1 chan UART1: 1 channel	nnel/simplified I ² C: 1 channel					
Event link cor	ntroller (ELC)	Event input: 18		Event input: 19				
		Event trigger output: 6		Event trigger output: 6				
Vectored	Internal		20					
interrupt sources	External	6	;	7				
Key interrupt		_	_					
Reset		Reset by RESET pin		•				
		Internal reset by watchdog time	er					
		Internal reset by power-on-res	et					
		Internal reset by voltage detection						
		Internal reset by illegal instruction						
		Internal reset by RAM parity e						
		Internal reset by illegal-memory	ry access					
Power-on-res	set circuit	Power-on-reset: 1.51 ±0.03 V Power-down-reset: 1.50 ±0.03 V						
Voltage detec	ctor	2.75 V to 4.06 V (6 stages)						
On-chip debu	g function	Provided	Provided					
Power supply	voltage	V _{DD} = 2.7 to 5.5 V						
Operating an	bient temperature	Ta = -40 to +85°C						

Note

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS

Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted are as follows according to product.

2.1 Pins Mounted According to Product

2.1.1 Port functions

Refer to 2.1.1 30-pin products, 2.1.2 32-pin products, and 2.1.3 44-pin products in the RL78/G1G User's Manual.

2.1.2 Non-port functions

Refer to 2.2.1 With functions for each product in the RL78/G1G User's Manual.



2.2 Absolute Maximum Ratings

Absolute Maximum Ratings

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Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V _{DD} +0.3 ^{Note 1}	
Input voltage	VI1	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P121 to P124, P137, P146, P147, EXCLK, RESET	-0.3 to V _{DD} +0.3 Note 2	<
Output voltage	Vo1	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	VAI1	ANI0 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 Notes 2, 3 and -0.3 to AVREF (+) +0.3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

Absolute Maximum Ratings

ratings are not exceeded.

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Parameter	Symbol		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	-40	mA
		Total of all	P00, P01, P40, P41, P120	-70	mA
		pins -170 mA	P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	40	mA
		Total of all	P00, P01, P40, P41, P120	70	mA
		pins 170 mA	P10 to P17, P30, P31, P50, P51, P60 to P63, P70 to P73, P146, P147	100	mA
	IOL2	Per pin	P20 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal o	pperation mode	-40 to +85	°C
temperature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum

2.3 Oscillator Characteristics

2.3.1 X1 oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator					

Note

Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution

Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G1G User's Manual.

2.3.2 On-chip oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le VDD \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator	fін		1		24	MHz
clock frequency Notes 1, 2	fносо		1		48	
High-speed on-chip oscillator			-2		+2	%
clock frequency accuracy						
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.4 DC Characteristics

2.4.1 Pin characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	$2.7~\textrm{V} \leq \textrm{Vdd} \leq 5.5~\textrm{V}$			-10.0 Note 2	mA
		Total of P00, P01, P40, P41, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			-55.0	mA
		(When duty ≤ 70% Note 3)	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-10.0	mA
		Total of P10 to P17, P30, P31,	$4.0~V \leq V_{DD} \leq 5.5~V$			-80.0	mA
		P50, P51, P60 to P63, P70 to P73, P146, P147 (When duty ≤ 70% Note 3)	2.7 V ≤ V _{DD} < 4.0 V			-19.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			-135.0	mA
	Іон2	Per pin for P20 to P27	$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.7~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.

Note 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH \times 0.7)/(n \times 0.01)

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P10, P15, P17, P30, P50, P51 do not output high level in N-ch open-drain mode.

Note 2. Do not exceed the total current value.

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147				20.0 Note 2	mA
		Total of P00, P01, P40, P41, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			70.0	mA
		(When duty $\leq 70\%$ Note 3)	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			15.0	mA
		Total of P10 to P17, P30, P31,	$4.0~V \leq V_{DD} \leq 5.5~V$			80.0	mA
		P50, P51, P60 to P63, P70 to P73, P146, P147 (When duty ≤ 70% Note 3)	2.7 V ≤ V _{DD} < 4.0 V			35.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	IOL2	Per pin for P20 to P27				0.4 Note 2	mA
		Total of all pins $(When \ duty \le 70\% \ ^{Note \ 3})$	$2.7~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- Note 2. However, do not exceed the total current value.
- $\textbf{Note 3.} \qquad \text{Specification under conditions where the duty factor} \leq 70\%.$

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120 to P124, P146, P147	Normal input buffer	0.8 VDD		VDD	V
	VIH2	P01, P10, P15 to P17, P30, P31, P50	TTL input buffer $4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	2.2		VDD	V
			TTL input buffer 3.3 V ≤ VDD < 4.0 V	2.0		VDD	V
			TTL input buffer 2.7 V ≤ VDD < 3.3 V	1.50		VDD	V
	VIH3	P20 to P27		0.7 Vdd		VDD	V
	VIH4	EXCLK, RESET		0.8 VDD		VDD	V
Input voltage, low	VIL1	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120 to P124, P146, P147	Normal input buffer	0		0.2 VDD	٧
	VIL2	P01, P10, P15 to P17, P30, P31, P50	TTL input buffer $4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer 3.3 V ≤ VDD < 4.0 V	0		0.5	V
			TTL input buffer 2.7 V ≤ VDD < 3.3 V	0		0.32	V
	VIL3	P20 to P27		0		0.3 VDD	V
	VIL4	EXCLK, RESET		0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P10, P15, P17, P30, P50, and P51 is VDD, even in the N-ch open-drain mode.

(Ta = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63,	4.0 V ≤ VDD ≤ 5.5 V, IOH1 = -10.0 mA	VDD - 1.5			V
			4.0 V ≤ VDD ≤ 5.5 V, IOH1 = -3.0 mA	VDD - 0.7			V
		$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ IOH1 = -2.0 mA	VDD - 0.6			٧	
			$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V},$ IOH1 = -1.0 mA	VDD - 0.5			V
	VOH2	P20 to P27	$2.7~V \le V$ DD $\le 5.5~V$, I OH2 = -100 μ A	VDD - 0.5			V
Output voltage, low	VOL1	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63,	$4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V},$ IOL1 = 20.0 mA			1.3	V
		P70 to P73, P120, P146, P147	4.0 V ≤ VDD ≤ 5.5 V, IOL1 = 8.5 mA			0.7	V
			$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V},$ $\text{IOL1} = 3.0 \text{ mA}$			0.6	V
			2.7 V ≤ VDD ≤ 5.5 V, IOL1 = 1.5 mA			0.4	V
		$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V},$ $\text{IOL1} = 0.3 \text{ mA}$			0.4	V	
	VOL2	P20 to P27	$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL2} = 400~\mu A$			0.4	V

Caution P00, P10, P15, P17, P30, P50, and P51 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditi	ions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P123, P124, P137, P146, P147, RESET					1	μА
	ILIH2	P121, P122 (X1, X2, EXCLK)	VI = VDD	In input port or external clock input			1	μА
				In resonator connection			10	μА
Input leakage current, low	ILIL1	P00, P01, P10 to P17, P20 to P27, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P123, P124, P137, P146, P147, RESET	Vi = Vss				-1	μΑ
	ILIL2	P121, P122 (X1, X2, EXCLK)	VI = VSS	In input port or external clock input			-1	μА
				In resonator connection			-10	μА
On-chip pull-up resistance	Ru	P00, P01, P10 to P17, P30, P31, P40, P41, P50, P51, P60 to P63, P70 to P73, P120, P146, P147	VI = Vss, ir	n input port	10	20	100	kΩ

2.4.2 Supply current characteristics

(1) Flash ROM: 16 KB of 30- pin to 44-pin products

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-speed	fносо = 48 MHz,	Basic	V _{DD} = 5.0 V		1.8		mA
current		main) mode Notes 3, 4	fih = 24 MHz	operation	V _{DD} = 3.0 V		1.8			
Note 1			HS (high-speed	fносо = 48 MHz,	Normal	V _{DD} = 5.0 V		3.9	6.9	mA
			main) mode Notes 3, 4	fih = 24 MHz	operation	V _{DD} = 3.0 V		3.9	6.9	
				fhoco = 24 MHz,	Normal	V _{DD} = 5.0 V		3.7	6.3	
				fih = 24 MHz	operation	V _{DD} = 3.0 V		3.7	6.3	
			fHOCO = 16 MHz,	Normal	V _{DD} = 5.0 V		2.8	4.6		
	fiH = 16 MHz operation $V_{DD} = 3.0 \text{ V}$	V _{DD} = 3.0 V		2.8	4.6					
			LS (low-speed main)	fiн = 8 MHz	Normal	V _{DD} = 3.0 V		1.2	2.0	mA
	mode Notes 3, 4		operation							
			HS (high-speed	fмх = 20 MHz,	Normal	Square wave input		3.1	5.3	mA
			main) mode Notes 2, 4	V _{DD} = 5.0 V	operation	Resonator connection		3.3	5.5	
				fmx = 20 MHz,	Normal	Square wave input		3.1	5.3	Ì
				V _{DD} = 3.0 V	operation	Resonator connection		3.3	5.5	
				fmx = 10 MHz,	Normal	Square wave input		2.0	3.1	Ì
				V _{DD} = 5.0 V	operation	Resonator connection		2.0	3.2	
			fmx = 10 MHz,	Normal	Square wave input		2.0	3.1	Î	
		V _{DD} = 3.0 V	operation	Resonator connection		2.0	3.2			
		LS (low-speed main)	fmx = 8 MHz,	Normal	Square wave input		1.2	1.9	mA	
			mode Notes 2, 4	V _{DD} = 3.0 V	operation	Resonator connection		1.2	2.0	

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, watchdog timer, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
- **Note 2.** When high-speed on-chip oscillator is stopped.
- **Note 3.** When high-speed system clock is stopped.
- Note 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

 HS (high speed main) mode: VDD = 2.7 V to 5.5 V@1 MHz to 24 MHz

 LS (low speed main) mode: VDD = 2.7 V to 5.5 V@1 MHz to 8 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

(1) Flash ROM: 16 KB of 30-pin to 44-pin products

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol		Co	nditions		MIN.	TYP.	MAX.	Unit	
Supply	IDD2	HALT mode	HS (high-speed	fносо = 48 MHz,	V _{DD} = 5.0 V		0.60	2.40	mA	
current	Note 2		main) mode Notes 4, 6	fih = 24 MHz	V _{DD} = 3.0 V		0.60	2.40		
Note 1				fHOCO = 24 MHz,	V _{DD} = 5.0 V		0.40	1.83		
				fih = 24 MHz	V _{DD} = 3.0 V		0.40	1.83		
				fHOCO = 16 MHz,	V _{DD} = 5.0 V		0.38	1.38		
				fін = 16 MHz	V _{DD} = 3.0 V		0.38	1.38		
			LS (low-speed main)	fih = 8 MHz	V _{DD} = 3.0 V		260	710	μΑ	
			mode Notes 4, 6							
				HS (high-speed	fmx = 20 MHz,	Square wave input		0.28	1.55	mA
		main) mode Notes 3,	main) mode Notes 3, 6	V _{DD} = 5.0 V	Resonator connection		0.42	1.74		
				fmx = 20 MHz,	Square wave input		0.28	1.55		
				V _{DD} = 3.0 V	Resonator connection		0.42	1.74		
		-		fmx = 10 MHz,	Square wave input		0.19	0.86		
			$V_{DD} = 5.0 V$	Resonator connection		0.27	0.93			
				fmx = 10 MHz,	Square wave input		0.19	0.86		
				V _{DD} = 3.0 V	Resonator connection		0.27	0.93		
			LS (low-speed main)	fmx = 8 MHz,	Square wave input		95	550	μΑ	
			mode Notes 3, 6	VDD = 3.0 V	Resonator connection		145	590		
	IDD3	STOP	TA = -40°C	1	-1		0.18	0.51	μА	
	mode Note 5	TA = +25°C				0.24	0.51			
		TA = +50°C			0.29			1		
			TA = +70°C				0.41	1.90		
			Ta = +85°C				0.90	3.30		

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, comparator, programmable gain amplifier, watchdog timer, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors.
- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator is stopped.
- Note 4. When high-speed system clock is stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When watchdog timer is stopped. The values below the MAX. column include the leakage current.
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

 HS (high speed main) mode: VDD = 2.7 V to 5.5 V@1 MHz to 24 MHz

 LS (low speed main) mode: VDD = 2.7 V to 5.5 V@1 MHz to 8 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

(2) Peripheral Functions (Common to all products)

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le VDD \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
12-bit interval timer operating current	IIT Notes 1, 8					0.02		μА
Watchdog timer operating current	IWDT Notes 1, 2	fiL = 15 kHz				0.22		μА
A/D converter	I _{ADC} Note 3	When conversion	Normal mode, AVRE	P = VDD = 5.0 V		1.3	1.7	mA
operating current		at maximum speed	Low voltage mode, A	AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF					75		μА
Temperature sensor operating current	ITMPS					75		μА
Comparator operating	ICMP Note 4	Per channel of	When the comparate	or is operating		45.0	65.0	μΑ
current		comparator 1	When the comparator is stopped			0.0	0.1	i
Programmable gain	IPGA Note 5	When the programmable gain amplifier is operating				240.0	340.0	μΑ
amplifier operating current		When the program		0.0	0.1			
LVD operating current	I _{LVI} Note 6					0.08		μА
SNOOZE operating	Isnoz	ADC operation	The mode is perform	ned Note 7		0.50	0.60	mA
current			The A/D conversion operations are performed	Low voltage mode AVREFP = VDD = 3.0 V		1.20	1.44	mA
		CSI/UART operati	on			0.70	0.84	mA

- Note 1. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 2. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The current value of the RL78 microcontroller is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates in STOP mode.
- Note 3. Current flowing only to the A/D converter. The current value of the RL78 microcontroller is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **Note 4.** Current flowing only to the comparator. The current value of the RL78 microcontroller is the sum of IDD1 or IDD2 and ICMP when the comparator operates in operating mode or HALT mode.
- Note 5. Current flowing only to the programmable gain amplifier. The current value of the RL78 microcontroller is the sum of IDD1 or IDD2 and IPGA when the programmable gain amplifier operates in operating mode or HALT mode.
- Note 6. Current flowing only to the LVD circuit. The current value of the RL78 microcontroller is the sum of IDD1, IDD2 or IDD3 and ILVI when the LVD circuit operates in the Operating, HALT or STOP mode.
- Note 7. For details on the transition time to SNOOZE mode, refer to 18.3.3 SNOOZE mode in the RL78/G1G User's Manual.
- Note 8. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontroller is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fclk: CPU/peripheral hardware clock frequency
- Remark 3. Temperature condition of the TYP. value is TA = 25°C

2.5 AC Characteristics

2.5.1 Basic operation

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

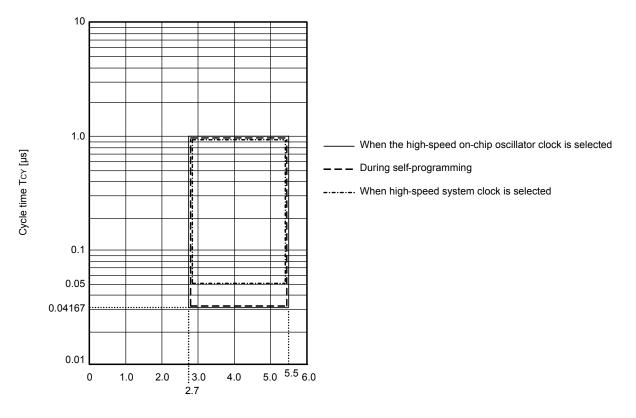
Items	Symbol		Condition	ns	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Tcy	Main system clock (fMAIN)	HS (high-speed main) mode	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	0.04167		1	μS
		operation	LS (low-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.125		1	μS
		In the self programming	HS (high-speed main) mode	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	0.04167		1	μS
		mode	LS (low-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.125		1	μS
External main system clock frequency	fEX	2.7 V ≤ VDD ≤	5.5 V		1.0		20.0	MHz
External main system clock input high-level width, low-level width	texh, texl	2.7 V ≤ VDD ≤	5.5 V		24			ns
TI00 to TI03 input high-level width, low-level width	tтін, tтіL				1/fмск + 10			ns
Timer RJ input cycle	fc	TRJIO		$2.7~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$	100			ns
Timer RJ input high-level width, low-level width	fwH, fwL	TRJIO		2.7 V ≤ VDD ≤ 5.5 V	40			ns
TO00 to TO03,	fто	HS (high-spee	ed main) mode	$4.0 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			12	MHz
TRJIO0,TRJO,TRDIOA0/1,				$2.7 \text{ V} \le \text{VDD} \le 4.0 \text{ V}$			8	MHz
TRDIOB0/1, TRDIOC0/1,TRDIOD0/1 output frequency		LS (low-speed	l main) mode	$2.7~V \leq V_{DD} \leq 5.5~V$			4	MHz
PCLBUZ0, PCLBUZ1	fPCL	HS (high-spee	ed main) mode	$4.0 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			16	MHz
output frequency				2.7 V ≤ V _{DD} < 4.0 V			8	MHz
		LS (low-speed	l main) mode	$2.7~V \leq V_{DD} \leq 5.5~V$			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INTF	P5	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	1			μS
Key interrupt input low-level width	tkr	KR0-KR3		2.7 V ≤ VDD ≤ 5.5 V	250			ns
RESET low-level width	trsl				10			μS

Remark fmck: Timer array unit operation clock frequency

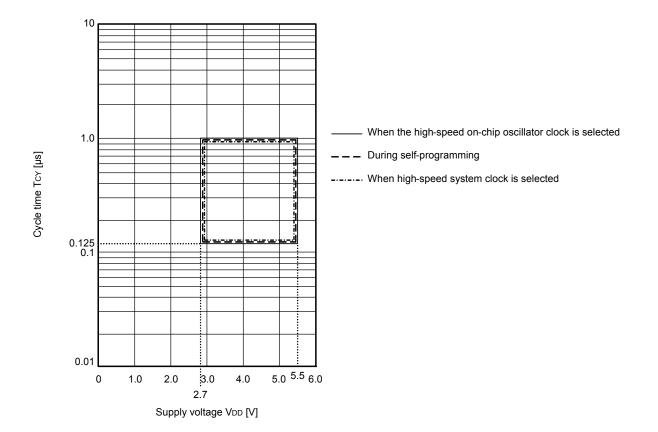
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

Minimum Instruction Execution Time during Main System Clock Operation

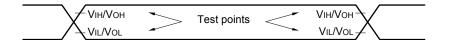
TCY vs VDD (HS (high-speed main) mode)



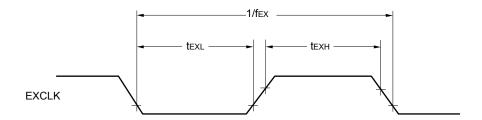
TCY vs VDD (LS (low-speed main) mode)



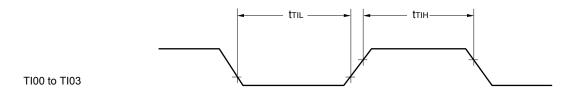
AC Timing Test Points

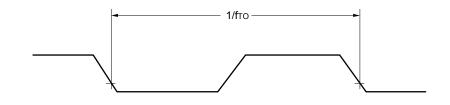


External System Clock Timing

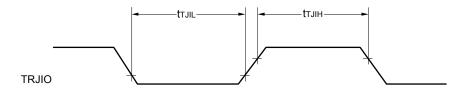


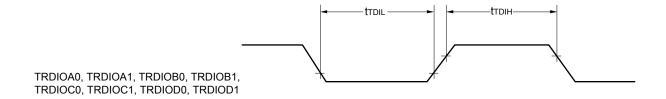
TI/TO Timing

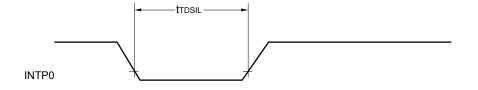




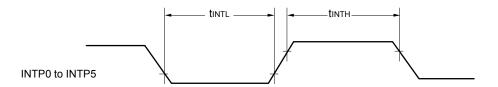
TO00 to TO03 TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1



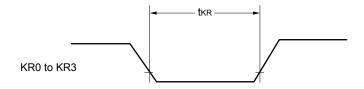




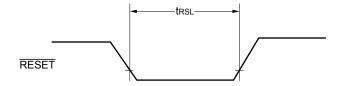
Interrupt Request Input Timing



Key Interrupt Input Timing

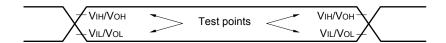


RESET Input Timing



2.6 Peripheral Functions Characteristics

AC Timing Test Points



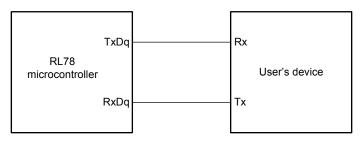
2.6.1 Serial array unit

(1) During communication at same potential (UART mode)

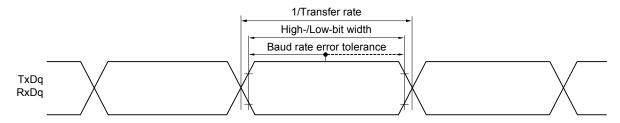
 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 2		4.0		1.3	Mbps

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

 $\label{eq:hspeed} \begin{array}{ll} \mbox{HS (high-speed main) mode:} & 24 \mbox{ MHz } (2.7 \mbox{ V} \le \mbox{VDD} \le 5.5 \mbox{ V}) \\ \mbox{LS (low-speed main) mode:} & 8 \mbox{ MHz } (2.7 \mbox{ V} \le \mbox{VDD} \le 5.5 \mbox{ V}) \\ \end{array}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 5)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	` • .	HS (high-speed main) mode		LS (low-speed main) mode	
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	83.3		250		ns
SCKp high-/low-level width	tkh1, tkl1	4.0 V ≤ V _{DD} ≤ 5.5 V		tkcy1/2 - 7		tксү1/2 - 50		ns
		2.7 V ≤ V _{DD} ≤	5.5 V		tксү1/2 - 50		ns	
SIp setup time (to SCKp↑) Note 1	tsıĸ1	$4.0 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$		23		110		ns
		2.7 V ≤ V _{DD} ≤	5.5 V	33		110		ns
SIp hold time (from SCKp↑) Note 2	tksi1	$2.7 \text{ V} \leq \text{V}_{DD} \leq$	5.5 V	10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note 4			10		10	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- $\textbf{Remark 1.} \ \ \textbf{This value is valid only when CSI00's peripheral I/O redirect function is not used.}$
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions H		HS (high-spee mode	d main)	LS (low-speed main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	167		500		ns
SCKp high-/low-level width	tkH1, tkL1	4.0 V ≤ V _{DD} ≤ 5.5 V tκ		tксү1/2 - 12		tксү1/2 - 50		ns
		2.7 V ≤ V _{DD} ≤	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			tксү1/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	4.0 V ≤ V _{DD} ≤	5.5 V	44		110		ns
		2.7 V ≤ V _{DD} ≤	5.5 V	44		110		ns
SIp hold time (from SCKp↑) Note 2	tksıı	2.7 V ≤ V _{DD} ≤	5.5 V	19		19		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1		2.7 V ≤ V _{DD} ≤ 5.5 V C = 30 pF ^{Note 4}		25		25	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)
- Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) $(TA = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

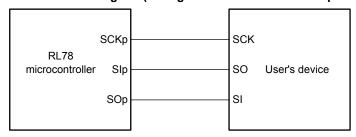
Parameter	Symbol	Conc	HS (high-speed main) mode		LS (low-spe	Unit		
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	20 MHz < fmck	8/fмск		_		ns
			fмcк ≤ 20 MHz	6/fмск		6/fмск		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	16 MHz < fmck	8/fмск		_		ns n
			fмск ≤ 16 MHz	6/fмск		6/fмск		ns
SCKp high-/low-level width	tĸн2,	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		tkcy2/2 - 7		tkcy2/2 - 7		ns
	tKL2	2.7 V ≤ V _{DD} ≤ 5.5 V		tkcy2/2 - 8		tkcy2/2 - 8		ns
SIp setup time (to SCKp↑) Note 1	tsık2	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$		1/fмск + 20		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 2	tksı2	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		2/fмcк + 44		2/fмск + 110	ns
SSI00 setup time	tssık	DAPmn = 0	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	120		120		ns
		DAPmn = 1	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	1/fмск + 120		1/fмск + 120		ns
SSI00 hold time	tĸssı	DAPmn = 0	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	1/fмск + 120		1/fмск + 120		ns
		DAPmn = 1	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	120		120		ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)
- Remark 2. fmck: Serial array unit operation clock frequency

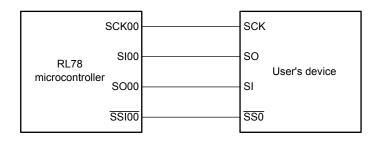
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00))

CSI mode connection diagram (during communication at same potential)



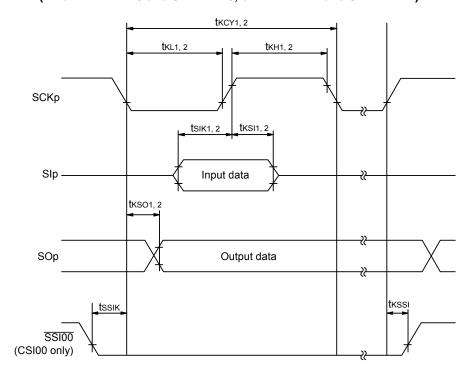
CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



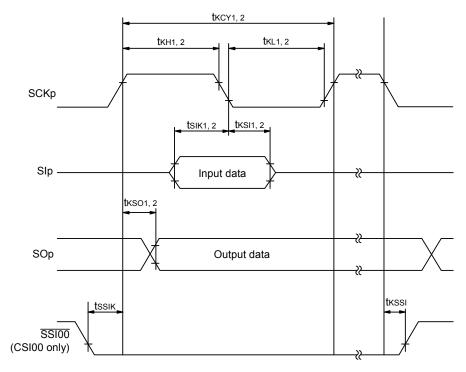
Remark 1. p: CSI number (p = 00)

Remark 2. m: Unit number, n: Channel number (mn = 00)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00)

Remark 2. m: Unit number, n: Channel number (mn = 00)

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

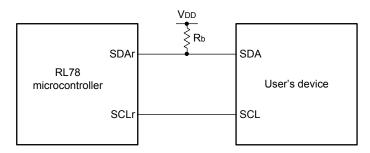
Parameter	Symbol	Conditions	HS (high-speed	d main) mode	LS (low-speed	main) mode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		400 Note 1	kHz
		$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$		400 Note 1		400 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		ns
		$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1150		1150		ns
Hold time when SCLr = "H"	thigh	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	1150		1150		ns
Data setup time (reception)	tsu: dat	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/fmck + 85 Note 2		1/fмск + 145 Note 2		ns
		$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1/fмск + 145 Note 2		1/fмск + 145 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	0	305	0	305	ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	0	355	0	355	ns

Note 1. The value must also be equal to or less than fmck/4.

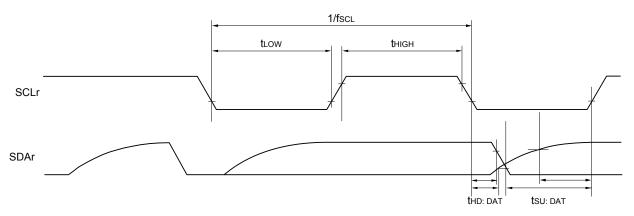
Note 2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

(Remaks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

 $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] : \mathsf{Communication line (SDAr) pull-up resistance}, \ \, \mathsf{Cb[F]} : \mathsf{Communication line (SDAr, SCLr) load capacitance}$

Remark 2. r: IIC number (r = 00), g: PIM number (g = 3, 5), h: POM number (h = 3, 5)

Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0), mn = 00)

(6) Communication at different potential (2.5 V, 3 V) (UART mode)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol		Conditions	HS (high-sp	eed main) mode	LS (low-spee	ed main) mode	Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	ception $4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$		f _{MCK} /6 Note 1		fmck/6 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		4.0		1.3	Mbps
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		fmck/6 Note 1		f _{MCK} /6 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3	Mbps
			2.7 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. Use it with $VDD \ge Vb$.

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$) LS (low-speed main) mode: 8 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 5)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)

Remark 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

 $4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_{b} \leq 4.0~V;~V_{IH}$ = $2.2~V,~V_{IL}$ = 0.8~V

 $2.7~V \le V_{DD} \le 4.0~V$, $2.3~V \le V_{b} \le 2.7~V$: VIH = 2.0~V, VIL = 0.5~V

 $2.7~\text{V} \leq \text{Vdd}$ < $3.3~\text{V},~1.6~\text{V} \leq \text{Vb} \leq 2.0~\text{V};~\text{ViH}$ = 1.50~V,~ViL = 0.32~V

(6) Communication at different potential (2.5 V, 3 V) (UART mode)

$(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol		Conditions	HS (high-spe	ed main) mode	LS (low-spee	d main) mode	Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	$ 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_{b} \leq 4.0 \ V $		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega,$ $V_b = 2.7 \text{ V}$		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega,$ $V_b = 2.3 \text{ V}$		1.2 Note 4		1.2 Note 4	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		Note 5, 6		Note 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\left\{-C_b \times R_b \times ln \left(1 - \frac{2.2}{V_b}\right)\right\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} }{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits} }$$

- **Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met.
 - Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In} (1 - \frac{2.0}{\text{Vb}})\} }{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits} }$$

- Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- Note 5. Use it with $VDD \ge Vb$.



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

Note 6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.7 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In} (1 - \frac{1.5}{\text{Vb}})\}}{\times 100 \, [\%]}$$

$$(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}$$

- Note 7. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remark 1.** $Rb[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- **Remark 2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 5)
- Remark 3. fMcK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03))

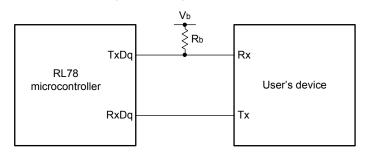
Remark 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in UART mode.

$$4.0 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V}; \text{ Vih} = 2.2 \text{ V}, \text{ Vil} = 0.8 \text{ V}$$

$$2.7 \text{ V} \leq \text{VDD} \leq 4.0 \text{ V}, 2.3 \text{ V} \leq \text{Vb} \leq 2.7 \text{ V}; \text{ Vih} = 2.0 \text{ V}, \text{ Vil} = 0.5 \text{ V}$$

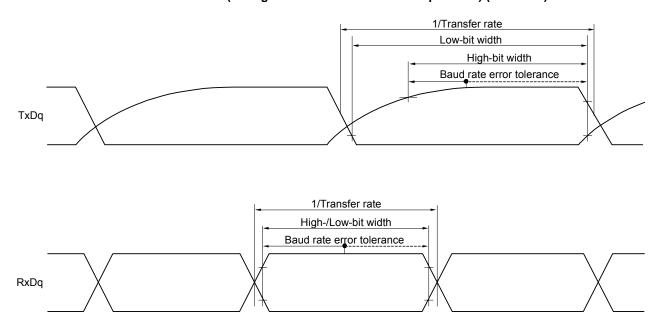
$$2.7 \text{ V} \leq \text{VDD} \leq 3.3 \text{ V}, 1.6 \text{ V} \leq \text{Vb} \leq 2.0 \text{ V}; \text{ Vih} = 1.50 \text{ V}, \text{ Vil} = 0.32 \text{ V}$$

UART mode connection diagram (during communication at different potential)



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

UART mode bit width (during communication at different potential) (reference)



Remark 1. Rb[Ω]: Communication line (TxDq) pull-up resistance, Vb[V]: Communication line voltage **Remark 2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 5)

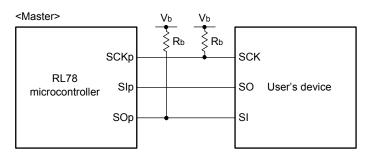
(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-speed mode	d main)	Unit
					MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	200		1150		ns
			$ \begin{aligned} &2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ &C_{b} = 20 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned} $	300		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ $C_b = 20 \text{ pF}, R_b =$	$\begin{array}{l} 5 \text{ V, } 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V,} \\ 1.4 \text{ k}\Omega \end{array}$	tkcy1/2 - 50		tkcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0$ C _b = 20 pF, R _b =	$0 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ 2.7 kΩ	tксү1/2 - 120		tксү1/2 - 120		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	$5 \text{ V}, 2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$ $1.4 \text{ k}\Omega$	tkcy1/2 - 7		tkcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0$ C _b = 20 pF, R _b =	0 V, $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$, $2.7 \text{ k}\Omega$	tkcy1/2 - 10		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	$5 \text{ V}, 2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$ $1.4 \text{ k}\Omega$	58		479		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0$ C _b = 20 pF, R _b =	0 V, $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$, $2.7 \text{ k}\Omega$	121		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksii	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	5 V, 2.7 V \leq V _b \leq 4.0 V, 1.4 k Ω	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0$ C _b = 20 pF, R _b =	0 V, $2.3 \text{ V} \le \text{V}_\text{b} \le 2.7 \text{ V}$, $2.7 \text{ k}\Omega$	10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	$\begin{array}{l} 5 \text{ V, } 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V,} \\ 1.4 \text{ k}\Omega \end{array}$		60		60	ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0$ C _b = 20 pF, R _b =	0 V, $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$, $2.7 \text{ k}\Omega$		130		130	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	$\begin{array}{l} 5 \text{ V, } 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V,} \\ 1.4 \text{ k}\Omega \end{array}$	23		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0$ C _b = 20 pF, R _b =	$0 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ 2.7 kΩ	33		110		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksıı	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ $C_b = 20 \text{ pF}, R_b =$	$0.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ 0.4 k	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0$ C _b = 20 pF, R _b =	0 V, $2.3 \text{ V} \le \text{V}_\text{b} \le 2.7 \text{ V}$, $2.7 \text{ k}\Omega$	10		10		ns
Delay time from SCKp↑ to SOp output Note 2	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5$ C _b = 20 pF, R _b =	5 V, 2.7 V \leq V _b \leq 4.0 V, 1.4 k Ω		10		10	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0$ C _b = 20 pF, R _b =	$0 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ 2.7 kΩ		10		10	ns

(Notes, Caution and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)
- Remark 3. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.
 - $4.0~V \le V_{DD} \le 5.5~V,~2.7~V \le V_{b} \le 4.0~V;~V_{IH} = 2.2~V,~V_{IL} = 0.8~V$ $2.7~V \le V_{DD} < 4.0~V,~2.3~V \le V_{b} \le 2.7~V;~V_{IH} = 2.0~V,~V_{IL} = 0.5~V$
- Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(8) Communication at different potential (2.5 V, 3 V) (fMC κ /4) (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, VSS = 0 V)(1/2)

Parameter	Symbol	nbol Conditions		HS (high-spee	,	LS (low-speed mode	d main)	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fcLk	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_{b} \leq 4.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 1.4 \ k\Omega \end{aligned} $	300		1150		ns
			$\begin{aligned} 2.7 & \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF, R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$	500		1150		ns
			$\begin{split} 2.7 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split}$	1150		1150		ns
SCKp high-level width	tkH1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.$ C _b = 30 pF, R _b =	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 k Ω	tkcy1/2 - 75		tkcy1/2 - 75		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ C _b = 30 pF, R _b =	0 V, 2.3 V \leq V _b \leq 2.7 V, \leq 2.7 k Ω	tkcy1/2 - 170		tксү1/2 - 170		ns
		2.7 V ≤ V _{DD} < 3. C _b = 30 pF, R _b =	3 V, 1.6 V \leq V _b \leq 2.0 V, = 5.5 kΩ	tkcy1/2 - 458		tксү1/2 - 458		ns
SCKp low-level width	tĸL1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.$ C _b = 30 pF, R _b =	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	tксү1/2 - 12		tkcy1/2 - 50		ns
		2.7 V ≤ V _{DD} < 4. C _b = 30 pF, R _b =	0 V, 2.3 V \leq V _b \leq 2.7 V, \leq 2.7 kΩ	tксү1/2 - 18		tkcy1/2 - 50		ns
		2.7 V ≤ V _{DD} < 3. C _b = 30 pF, R _b =	3 V, 1.6 V \leq V _b \leq 2.0 V, \leq 5.5 kΩ	tkcy1/2 - 50		tkcy1/2 - 50		ns

Caution 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Caution 2. Use it with $VDD \ge Vb$.

Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 3. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

 $4.0~V \le V_{DD} \le 5.5~V,~2.7~V \le V_{b} \le 4.0~V;~V_{IH} = 2.2~V,~V_{IL} = 0.8~V$ $2.7~V \le V_{DD} < 4.0~V,~2.3~V \le V_{b} \le 2.7~V;~V_{IH} = 2.0~V,~V_{IL} = 0.5~V$

(8) Communication at different potential (2.5 V, 3 V) (fMck/4) (CSI mode) (master mode, SCKp... internal clock output)

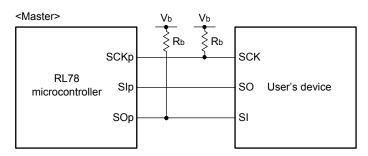
(Ta = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol	Conditions		peed main) ode		peed main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsik1	$ 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega $	81		479		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega $	177		479		ns
		$\label{eq:substitute} \begin{array}{l} 2.7~\text{V} \leq \text{V}_{\text{DD}} < 3.3~\text{V},~1.6~\text{V} \leq \text{V}_{\text{b}} \leq 2.0~\text{V},\\ \text{C}_{\text{b}} = 30~\text{pF},~R_{\text{b}} = 5.5~\text{k}\Omega \end{array}$	479		479		ns
SIp hold time (from SCKp↑) Note 1	tksıı	$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega $	19		19		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega $	19		19		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega $	19		19		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega $		100		100	ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega $		195		195	ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega $		483		483	ns
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega $	44		110		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega $	44		110		ns
		$2.7~V \leq V_{DD} < 3.3~V, \ 1.6~V \leq V_b \leq 2.0~V,$ $C_b = 30~pF, \ R_b = 5.5~k\Omega$	110		110		ns
SIp hold time (from SCKp↓) Note 2	tksi1	$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega $	19		19		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega $	19		19		ns
		$ 2.7 \; \text{V} \leq \text{V}_{DD} < 3.3 \; \text{V}, \; 1.6 \; \text{V} \leq \text{V}_{b} \leq 2.0 \; \text{V}, \\ \text{C}_{b} = 30 \; \text{pF}, \; \text{R}_{b} = 5.5 \; \text{k}\Omega $	19		19		ns
Delay time from SCKp↑ to SOp output Note 2	tkso1	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		25		25	ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		25		25	ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V},$ $C_{b} = 30 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega$		25		25	ns

(Notes, Caution and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential

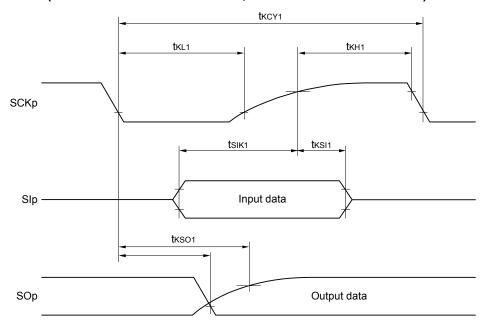


- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- Caution 2. Use it with $VDD \ge Vb$.
- **Remark 1.** Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)
- Remark 3. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

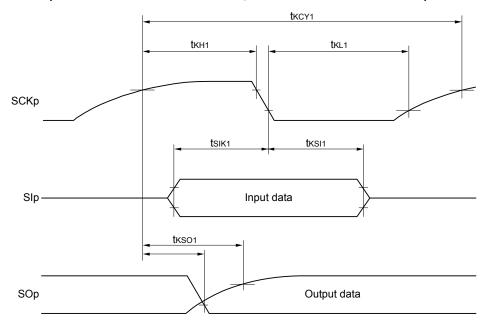
 $4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_{b} \leq 4.0~V;~V_{IH}$ = $2.2~V,~V_{IL}$ = 0.8~V

 $2.7~V \le V_{DD} \le 4.0~V$, $2.3~V \le V_{b} \le 2.7~V$: VIH = 2.0~V, VIL = 0.5~V

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



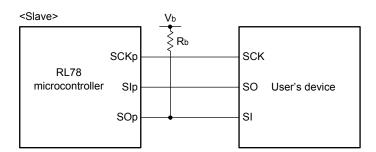
Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

(9) Communication at different potential (2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Sym bol	Co	nditions	, ,	speed main) ode	`	peed main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V,$	20 MHz < fмcк ≤ 24 MHz	12/fмск		_		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	10/fмск		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	16/fмск		_		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмcк ≤ 20 MHz	14/fмск		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		ns
		$1.6~V \leq V_b \leq 2.0~V$	16 MHz < fмcк ≤ 20 MHz	32/fмск		_		ns
			8 MHz < fмcк ≤ 16 MHz	26/fмск		_		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	10/fмск		10/fмск		ns
SCKp high-/low-level	tĸн2,	$4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, 2.7$	$7 \text{ V} \leq V_b \leq 4.0 \text{ V}$	tkcy2/2 - 12		tkcy2/2 - 50		ns
width	tKL2	2.7 V ≤ V _{DD} < 4.0 V, 2.3	3 V ≤ V _b ≤ 2.7 V	tkcy2/2 - 18		tkcy2/2 - 50		ns
		2.7 V ≤ V _{DD} < 3.3 V, 1.	$6~V \leq V_b \leq 2.0~V$	tkcy2/2 - 50		tkcy2/2 - 50		ns
SIp setup time (to SCKp↑) Note 2	tsık2	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$		1/fмск + 20		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 4	tkso2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2.0$ C _b = 30 pF, R _b = 1.4 kg	•		2/fмск + 120		2/fмск + 573	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.0 C _b = 30 pF, R _b = 2.7 kΩ	,		2/fмск + 214		2/fмск + 573	ns
		2.7 V ≤ V _{DD} < 3.3 V, 1.0 C _b = 30 pF, R _v = 5.5 kΩ	,		2/fмск + 573		2/fмск + 573	ns

(Notes, Caution and Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

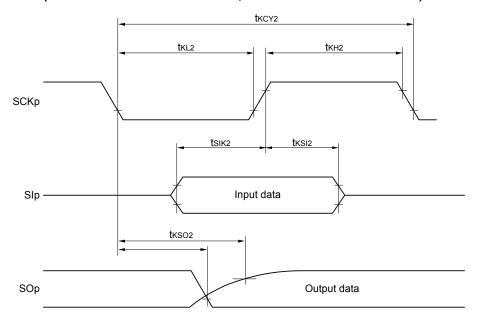


- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00))
- Remark 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in CSI mode.

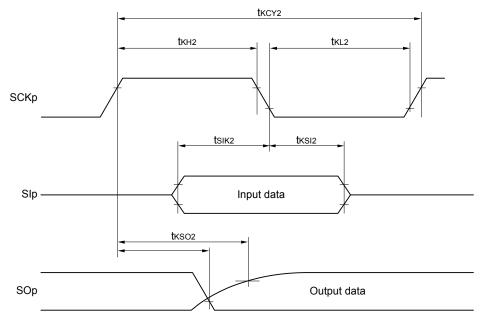
 $4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_{b} \leq 4.0~V;~V_{IH} = 2.2~V,~V_{IL} = 0.8~V$ $2.7~V \leq V_{DD} < 4.0~V,~2.3~V \leq V_{b} \leq 2.7~V;~V_{IH} = 2.0~V,~V_{IL} = 0.5~V$

Remark 5. Communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 2. Communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

(10) Communication at different potential (2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol	Conditions	` `	peed main) ode	,	peed main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscl	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		300 Note 1	kHz
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} < 2.7 \text{ V},$ $C_{b} = 50 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$		1000 Note 1		300 Note 1	kHz
		$ 4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, $ $ C_{b} = 100 \text{ pF}, \ R_{b} = 2.8 \text{ k}\Omega $		400 Note 1		300 Note 1	kHz
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} < 2.7 \text{ V},$ C_{b} = 100 pF, R_{b} = 2.7 k Ω		400 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} < 2.0 \text{ V} \text{ Note 2}, $ $ C_{b} = 100 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega $		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1550		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ C_{b} = 50 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega $	475		1550		ns
		$ 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, $ $ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega $	1150		1550		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} < 2.7 \text{ V},$ C_{b} = 100 pF, R_{b} = 2.7 k Ω	1150		1550		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} < 2.0 \text{ V} \text{ Note 2}, $	1550		1550		ns
Hold time when SCLr = "H"	thigh	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	245		610		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ \text{C}_{b} = 50 \text{ pF}, \ \text{R}_{b} = 2.7 \text{ k}\Omega $	200		610		ns
		$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	675		610		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} < 2.7 \text{ V},$ C_{b} = 100 pF, R_{b} = 2.7 k Ω	600		610		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} < 2.0 \text{ V} \text{ Note 2}, $	610		610		ns

(Notes, Caution and Remarks are listed on the next page.)

(10) Communication at different potential (2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed n	nain)	LS (low-speed m	nain)	Unit
			MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{DD} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{b} \leq 4.0 \; \text{V}, \\ &\text{Cb} = 50 \; \text{pF}, \; \text{Rb} = 2.7 \; \text{k}\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} 2.7 & \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 & \text{V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ \text{C}_{b} = 50 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ &\text{Cb} = 100 \text{ pF}, \text{Rb} = 2.8 \text{ k}\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ \text{C}_{b} = 100 \text{ pF}, \text{R}_{b} = 2.7 \text{ k}\Omega $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$\begin{split} 2.7 \ & \text{V} \leq \text{V}_{DD} < 3.3 \ \text{V}, \\ 1.6 \ & \text{V} \leq \text{V}_{b} < 2.0 \ \text{V} \ \text{Note 2}, \\ \text{Cb} = 100 \ \text{pF}, \ & \text{Rb} = 5.5 \ \text{k}\Omega \end{split}$	1/fмск + 190 Note 3		1/fmck + 190 Note 3		ns
Data hold time (transmission)	thd:dat	$ \begin{aligned} 4.0 & \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ C_{b} = 50 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned} $	0	305	0	305	ns
		$ \begin{aligned} 2.7 & \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ C_{b} & = 50 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned} $	0	305	0	305	ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ &C_{b} = 100 \text{ pF}, \text{ Rb} = 2.8 \text{ k}\Omega \end{aligned} $	0	355	0	355	ns
		$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} < 2.7 \text{ V}, \\ \text{C}_{b} = 100 \text{ pF}, \text{R}_{b} = 2.7 \text{ k}\Omega $	0	355	0	355	ns
		$\label{eq:substitute} \begin{split} 2.7 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} < 2.0 \ V \ Note \ 2, \\ Cb &= 100 \ pF, \ Rb = 5.5 \ k\Omega \end{split}$	0	405	0	405	ns

Note 1. The value must also be equal to or less than fMCK/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

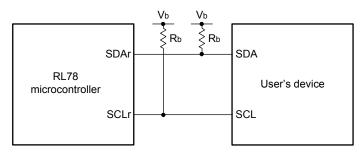
(Remarks are listed on the next page.)



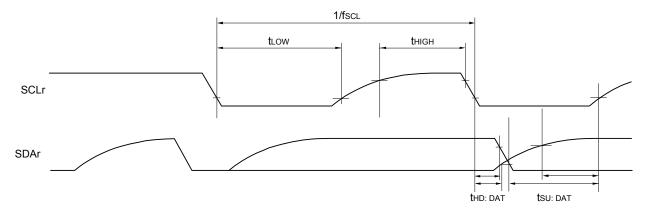
Note 2. Use it with $VDD \ge Vb$.

Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remark 1. Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00), g: PIM, POM number (g = 3, 5)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

 n: Channel number (n = 0), mn = 00)
- Remark 4. VIH and VIL below are observation points for the AC characteristics of the serial array unit when communicating at different potentials in simplified I²C mode.

$$4.0~V \le V_{DD} \le 5.5~V,~2.7~V \le V_{b} \le 4.0~V;~V_{IH} = 2.2~V,~V_{IL} = 0.8~V$$

$$2.7~V \le V_{DD} < 4.0~V,~2.3~V \le V_{b} \le 2.7~V;~V_{IH} = 2.0~V,~V_{IL} = 0.5~V$$

2.7 Analog Characteristics

2.7.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI7	Refer to 2.7.1 (1).	Refer to 2.7.1 (3).	Refer to 2.7.1 (4).
ANI16 to ANI19	Refer to 2.7.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.7.1 (1) .		_

(1) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI2 to ANI7

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Co	onditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		AVREFP = VDD	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error Notes 1, 2	EZS	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.25	% FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.25	% FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±1.5	LSB
Reference voltage (+)	AVREFP		•	2.7		VDD	V
Analog input voltage	VAIN			0		AVREFP	V
	VBGR	Select internal refe $2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ N}$ HS (high-speed ma	,	1.38	1.45	1.5	V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

(2) When AVREF (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI16 to ANI19

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Co	onditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		AVREFP = VDD	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error Notes 1, 2	EZS	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.35	% FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.35	% FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Reference voltage (+)	AVREFP		1	2.7		VDD	V
Analog input voltage	VAIN			0		AVREFP	V
	VBGR	Select internal refe $2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ N}$ HS (high-speed ma	,	1.38	1.45	1.5	V

Note 1. Excludes quantization error (±1/2 LSB).

(3) When AVREF (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), AVREF (-) = VSS (ADREFM = 0), target ANI pin: ANI0 to ANI7, ANI16 to ANI19

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	C	onditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.7~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error Notes 1, 2	EZS	10-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	% FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	% FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI7		0		VDD	V
		ANI16 to ANI19		0		VDD	V
	VBGR	Select internal reference voltage output, 2.7 V \leq VDD \leq 5.5 V, HS (high-speed main) mode		1.38	1.45	1.5	V

Note 1. Excludes quantization error (±1/2 LSB).

(4) When AVREF (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), AVREF (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI0 to ANI7, ANI16 to ANI19

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGR, Reference voltage (-) = AVREFM = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Co	Conditions			MAX.	Unit
Resolution	Res				8		bit
Conversion time	tconv	8-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	17		39	μS
Zero-scale error Notes 1, 2	EZS	8-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±1.0	LSB
Reference voltage (+)	VBGR			1.38	1.45	1.5	V
Analog input voltage	Vain			0		VBGR	V

Note 1. Excludes quantization error (±1/2 LSB).

2.7.2 Temperature sensor characteristics

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

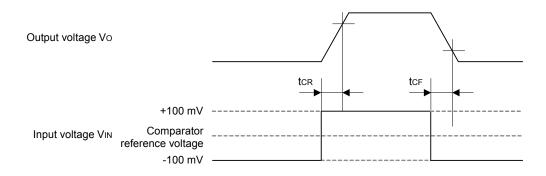
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Reference output voltage	VCONST	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μS

2.7.3 Comparator

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP				±5	±40	mV
Input voltage range	VICMP			0		Vdd	V
Internal reference voltage deviation	ΔVIREF	CmRVM register value: 7FH to 80H (m = 0, 1)				±2	LSB
		Other than above				±1	LSB
Response time	tcr, tcf	Input amplitude = :	±100 mV		70	150	ns
Operation stabilization time Note 1	tcmp	CMPnEN = 0→1	V _{DD} = 3.3 to 5.5 V			1	μS
			V _{DD} = 2.7 to 3.3 V			3	
Reference voltage stabilization wait time	tvr	CVRE: 0→1 Note 2				20	μS

- **Note 1.** Time required after the operation enable signal of the comparator has been changed (CMPnEN = $0 \rightarrow 1$) until a state satisfying the DC and AC characteristics of the comparator is entered.
- **Note 2.** Enable operation of internal reference voltage generation (CVREm bit = 1; m = 0, 1) and wait for the operation stabilization wait time before enabling the comparator output (CnOE bit = 1; n = 0, 1).



2.7.4 Programmable gain amplifier

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	C	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA				±5	±10	mV
Input voltage range	VIPGA			0		0.9 × VDD/gain	V
Response time	Vohpga			0.9 × V _{DD}			V
	Volpga					0.1 × VDD	
Gain error	_	4, 8 times	·			±1	%
		16 times				±1.5	
		32 times				±2	
Slew rate	SRRPGA	Rising edge	$4.0~V \leq V_{DD} \leq 5.5~V$	1.4			V/μs
			$2.7~V \leq V_{DD} \leq 4.0~V$	0.5			
	SRFPGA	Falling edge	$4.0~V \leq V_{DD} \leq 5.5~V$	1.4			
			$2.7~V \leq V_{DD} \leq 4.0~V$	0.5			
Operation stabilization wait time	tpga	4, 8 times				5	μS
Note		16, 32 times	16, 32 times			10	

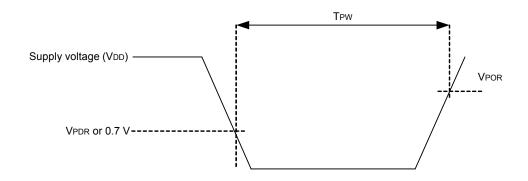
Note Time required after the PGA operation has been enabled (PGAEN = 1) until a state satisfying the DC and AC specifications of the PGA is entered.

2.7.5 POR circuit characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	V
	VPDR	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width Note	tpw		300			μS

Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.7.6 LVD circuit characteristics

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Para	meter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply	VLVD0	Power supply rise time	3.98	4.06	4.14	V
voltage	voltage level		Power supply fall time	3.90	3.98	4.06	V
		VLVD1	Power supply rise time	3.68	3.75	3.82	V
			Power supply fall time	3.60	3.67	3.74	V
		VLVD2	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		VLVD3	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		VLVD4	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		VLVD5	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pulse	width	tLW		300			μS
Detection delay	Detection delay time tLD					300	μS

Remark VLVD(n-1) > VLVDn: n = 1 to 5

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	itions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fal	2.70	2.75	2.81	V	
mode	VLVD4		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			(+0.1 V)	Falling interrupt voltage	2.80	2.86	2.91	V
	VLVD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			(+0.2 V)	Falling interrupt voltage	2.90	2.96	3.02	V
	VLVD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
	(+1.2	(+1.2 V)	Falling interrupt voltage	3.90	3.98	4.06	V	

2.7.7 Power supply voltage rising slope characteristics

 $(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.5 AC Characteristics.

2.8 RAM Data Retention Characteristics

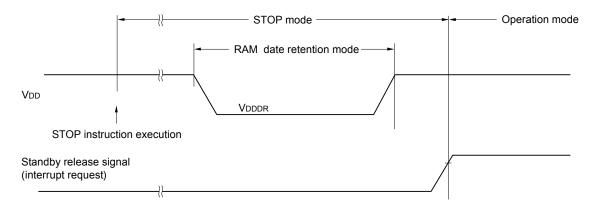
$(TA = -40 \text{ to } +85^{\circ}C)$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		5.5	V

Note

<R>

The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.9 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C Note 3	1,000			Times

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library.

Note 3. These specifications show the characteristics of the flash memory and the results obtained from Renesas Electronics reliability testing.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

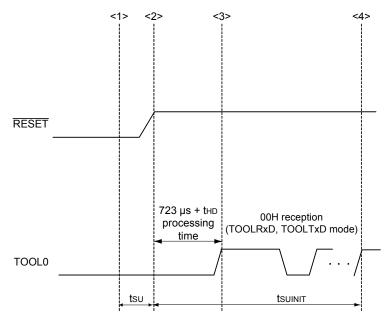
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps



2.11 Timing for Switching Flash Memory Programming Modes

(TA = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μS
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(the flash firmware processing time is excluded)

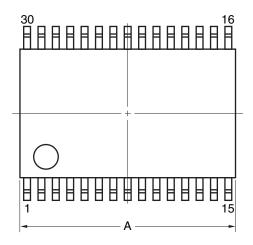
RL78/G1G 3. PACKAGE DRAWINGS

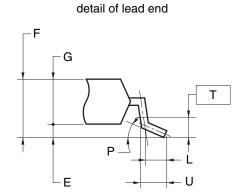
3. PACKAGE DRAWINGS

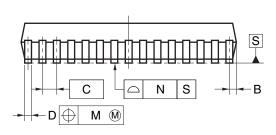
3.1 30-pin Products

R5F11EA8ASP, R5F11EAAASP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

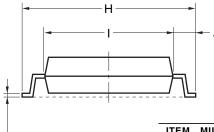






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



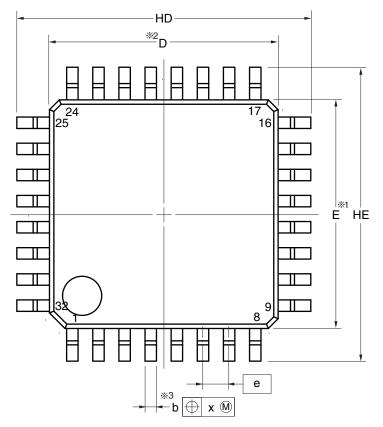
└ĸ

ITEM	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15

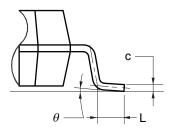
32-pin Products 3.2

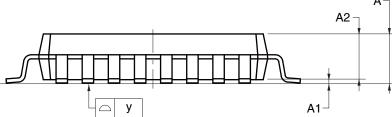
R5F11EB8AFP, R5F11EBAAFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2



detail of lead end





	(UNIT:mm)
ITEM	DIMENSIONS
D	7.00±0.10
Е	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
Α	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
С	0.145±0.055
L	0.50±0.20
θ	0° to 8°
е	0.80
х	0.20
у	0.10

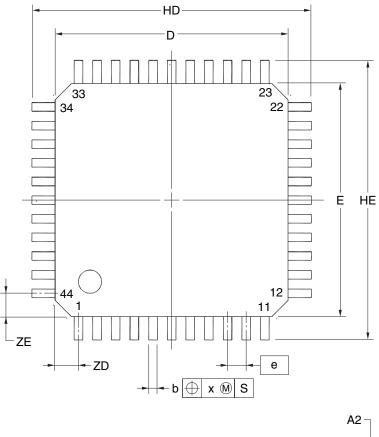
NOTE

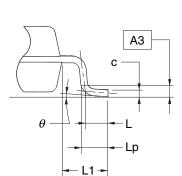
- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

44-pin Products 3.3

R5F11EF8AFP, R5F11EFAAFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36

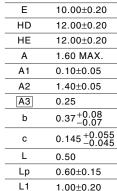




ITEM

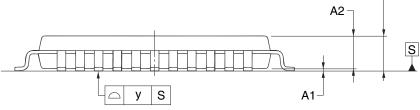
D

detail of lead end



(UNIT:mm) DIMENSIONS

10.00±0.20



Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

Α	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
АЗ	0.25
b	$0.37^{+0.08}_{-0.07}$
С	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	3°+5°
е	0.80
х	0.20
у	0.10
ZD	1.00
ZE	1.00

REVISION HISTORY	RL78/G1G Datasheet
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Rev.	Date	Description		
Nev.	Page		Summary	
1.00	Jul 31, 2014	_	First Edition issued	
1.20	Mar 25, 2015	1	1 Change of description in 1.1 Features	
		3	Change of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G1G	
		3	Change of Table 1 - 1 Orderable Part Numbers	
		11	Change of 1.6 Outline of Functions	
1.30	Sep 30, 2016	1	Addition of Note to 1.1 Features	
		4	Modification of Pin configuration in 1.3.1 30-pin products	
		5	Modification of Pin configuration in 1.3.2 32-pin products	
		6	Modification of Pin configuration in 1.3.3 44-pin products	
		63	Change of Note in 2.8 RAM Data Retention Characteristics	

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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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